SPN8898
N-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPN8898 is the N-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. The SPN8898 has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

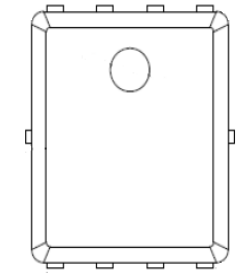
APPLICATIONS

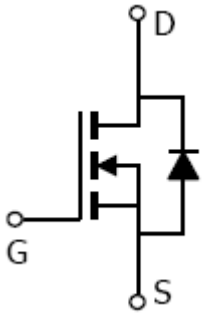
- DC/DC Converter
- Load Switch
- SMPS Secondary Side Synchronous Rectifier
- Motor Control
- Power Tool

FEATURES

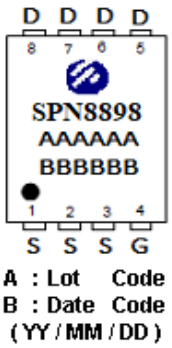
- 120V/20A,$R_{DS(ON)}$=17mΩ@V_{GS}=10V
- 120V/20A,$R_{DS(ON)}$=19.5mΩ@V_{GS}=4.5V
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- PPAK5x6-8L package design

PIN CONFIGURATION(PPAK5x6-8L)





PART MARKING



A : Lot Code
B : Date Code
(YY / MM / DD)

SPN8898
N-Channel Enhancement Mode MOSFET

PIN DESCRIPTION

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN8898DN8RGB	PPAK5x6-8L	SPN8898

※ SPN8898DN8RGB : Tape Reel ; Pb – Free ; Halogen - Free

ABSOULTE MAXIMUM RATINGS

(T_A=25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	120	V
Gate –Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Silicon Limited)	T_C=25℃	I_D	54	A
	T_C=100℃		34	
Pulsed Drain Current		I_{DM}	216	A
Single Pulse Avalanche Energy (T_C=25℃, L=0.1mH.)		E_{AS}	101	mJ
Power Dissipation	T_C=25℃	P_D	136	W
Operating Junction Temperature		T_J	-55/150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Case		$R_{\theta JC}$	0.92	℃/W

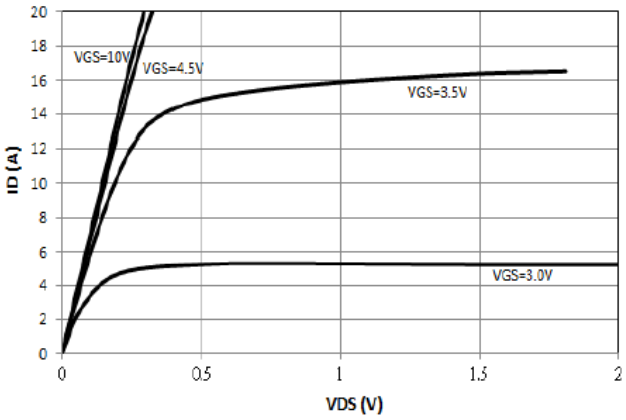
ELECTRICAL CHARACTERISTICS

(T_A=25℃ Unless otherwise noted)

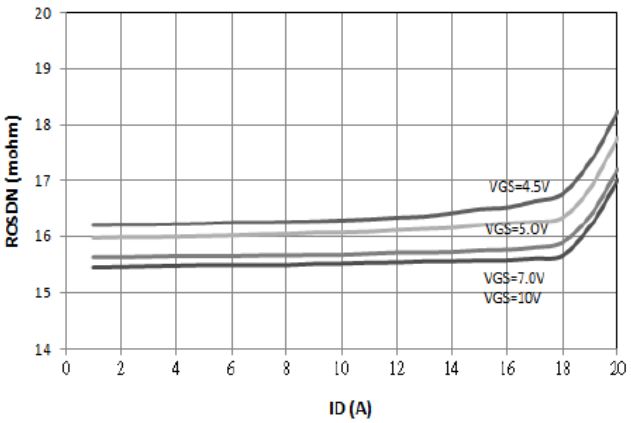
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	120			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	1.4	2.0	3.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=80V,V_{GS}=0V			1	uA
		V_{DS}=80V,V_{GS}=0V, T_J=125℃			10	
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=20A			17	mΩ
		V_{GS}=4.5V,I_D=20A			19.5	
Forward Transconductance	gfs	V_{DS}=10V,I_D=3A		10		S
Gate resistance	Rg	V_{DS}=0V,V_{GS}=0V f=1MHz		1.6		Ω
Diode Forward Voltage	V_{SD}	I_S=1A,V_{GS}=0V			1.0	V
Dynamic						
Total Gate Charge	Qg	V_{DS}=80V,V_{GS}=10V I_D=5A		66.7	100	nC
Gate-Source Charge	Q_{gs}			13.4	26	
Gate-Drain Charge	Q_{gd}			14.6	28	
Input Capacitance	C_{iss}	V_{DS}=50V,V_{GS}=0V f=1MHz		10773		pF
Output Capacitance	C_{oss}			233		
Reverse Transfer Capacitance	C_{rss}			155		
Turn-On Time	$t_{d(on)}$	V_{DD}=50V, I_D=1A,V_{GS}=10V R_G=3.3Ω		23	46	nS
	t_r			11	22	
Turn-Off Time	$t_{d(off)}$			57	114	
	t_f			26	58	

TYPICAL CHARACTERISTICS

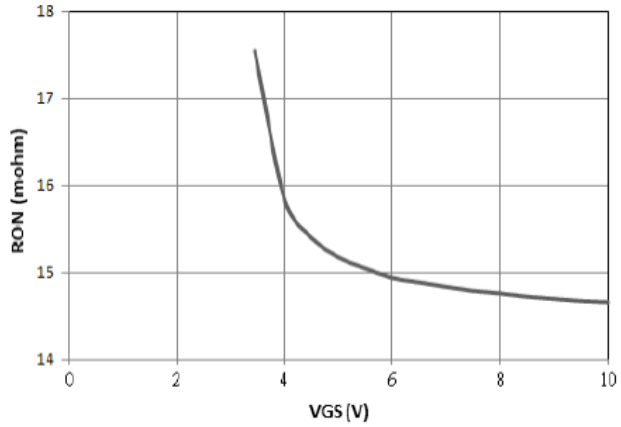
TYPICAL OUTPUT CHARACTERISTICS



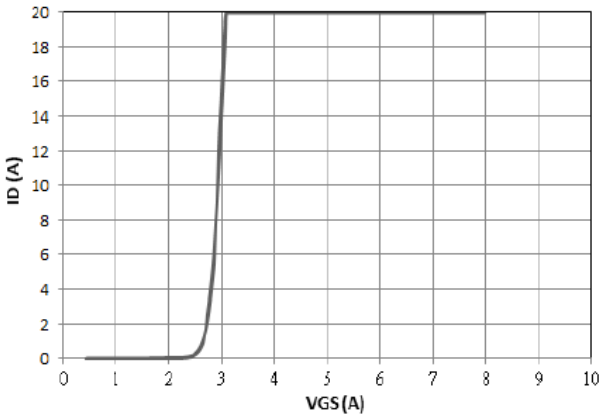
ON-RESISTANCE VS. DRAIN CURRENT ANDGATE VOLTAGE



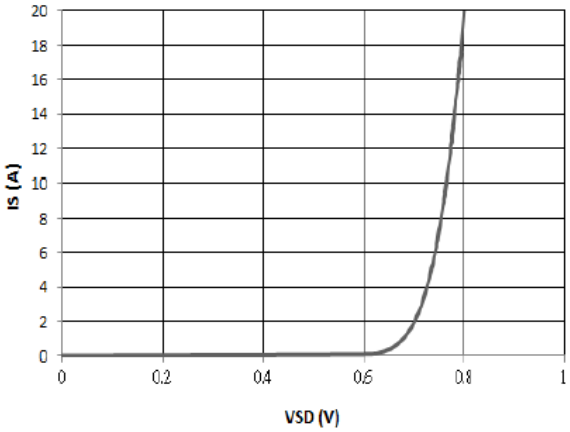
ON-RESISTANCE VS. GATE-SOURCE VOLTAGE



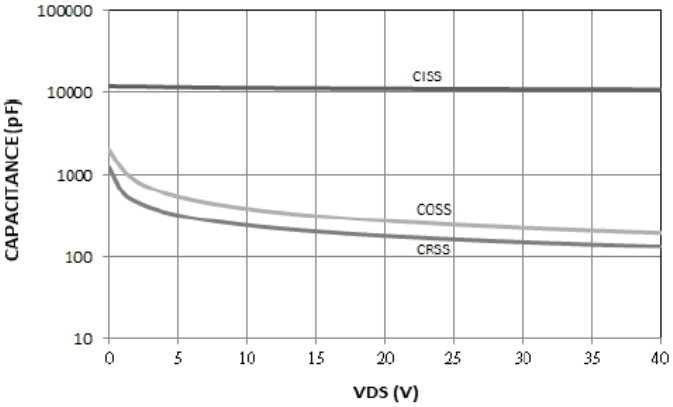
TYPICAL TRANSFER CHARACTERISTICS



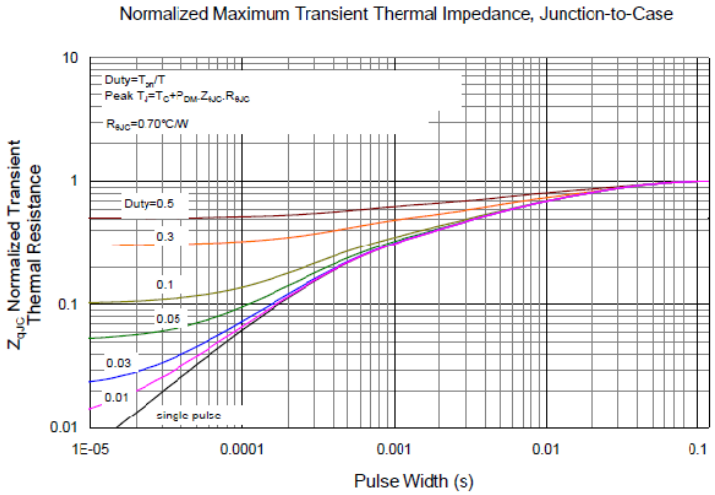
TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

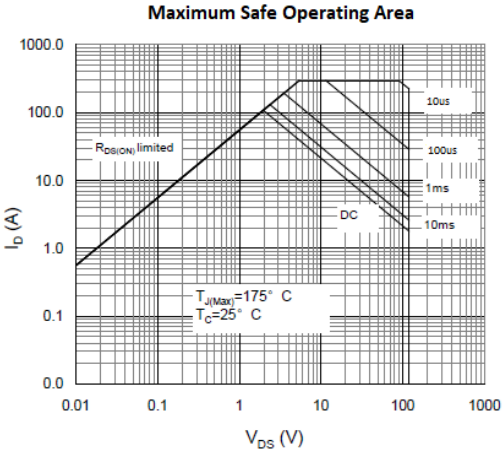


TYPICAL CAPACITANCE VS. DRAIN-SOURCE VOLTAGE



TYPICAL CHARACTERISTICS





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